

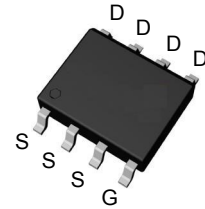
Features

- 100V/8A,
 $R_{DS(ON)} = 1.3 \text{ m}\Omega(\text{typ.}) @ V_{GS} = 10\text{V}$
 $R_{DS(ON)} = 1.8 \text{ m}\Omega(\text{typ.}) @ V_{GS} = 4.5\text{V}$
- Reliable and Rugged
- Lead Free and Green Devices Available
 (RoHS Compliant)

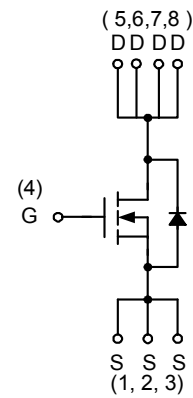
Applications

- Power Management in DC/DC Converter.

Pin Description



Top View of SOP-8



N-Channel MOSFET

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings (T _A =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		100	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _A =25°C	8	A
I _D	Continuous Drain Current	T _A =25°C	8	A
		T _A =70°C	6	
I _{DM} ^a	Pulsed Drain Current	T _A =25°C	24	A
P _D	Maximum Power Dissipation	T _A =25°C	3.5	W
		T _A =70°C	2.2	
R _{θJA}	Thermal Resistance-Junction to Ambient	t ≤ 10s	35	°C/W
		Steady State	70	°C/W
I _{AS} ^b	Avalanche Current, Single pulse (L=0.5mH)		18	A
E _{AS} ^b	Avalanche Energy, Single pulse (L=0.5mH)		81	mJ

Note a: Pulse width limited by maximum junction temperature.

b: UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J = 25^\circ\text{C}$).

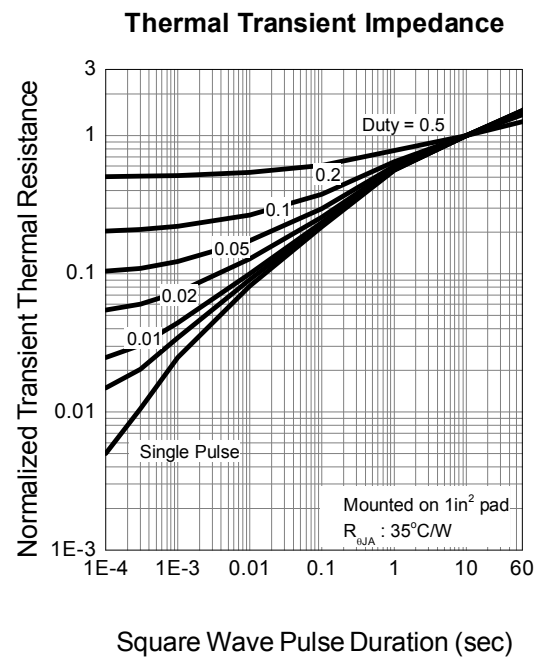
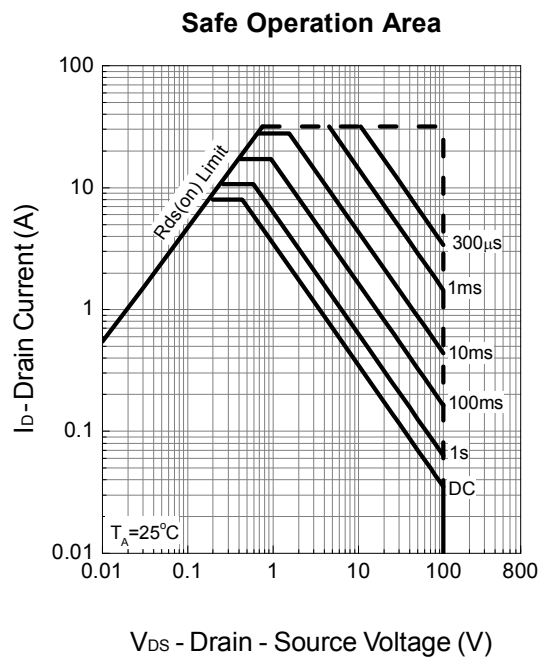
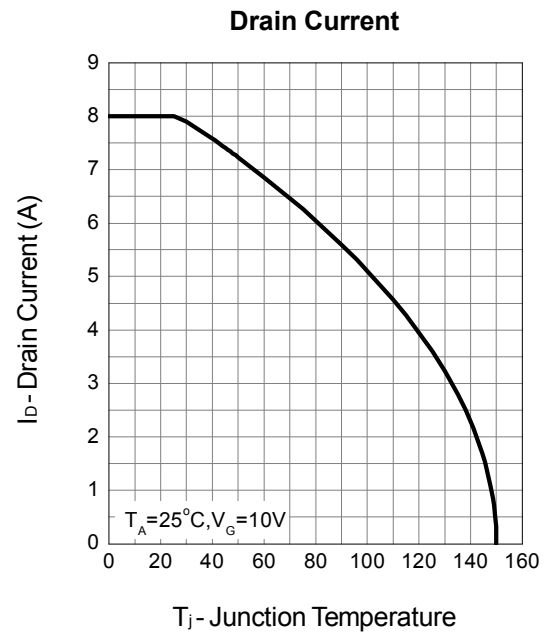
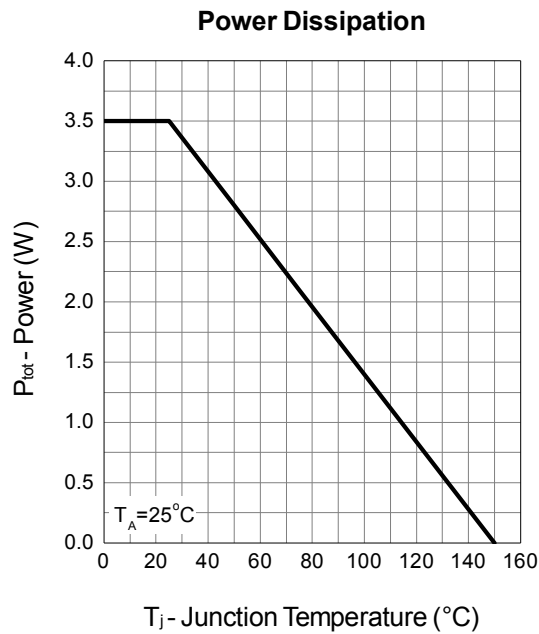
Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =80V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1	2	3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^c	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =8A	-	13	16	mΩ
		V _{GS} =4.5V, I _{DS} =6A	-	18	21	mΩ
Diode Characteristics						
V _{SD} ^c	Diode Forward Voltage	I _{SD} =5A, V _{GS} =0V	-	0.8	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =5A, dI _{SD} /dt=100A/μs	-	38	-	ns
Q _{rr}	Reverse Recovery Charge		-	76	-	nC
Dynamic Characteristics ^d						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	1.0	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, Frequency=1.0MHz	-	1200	1620	pF
C _{oss}	Output Capacitance		-	150	-	
C _{rss}	Reverse Transfer Capacitance		-	85	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _L =30Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	18	33	ns
t _r	Turn-on Rise Time		-	9	17	
t _{d(OFF)}	Turn-off Delay Time		-	56	101	
t _f	Turn-off Fall Time		-	14	26	
Gate Charge Characteristics ^d						
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =4.5V, I _{DS} =8A	-	24	-	nC
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =10V, I _{DS} =8A	-	50	65	
Q _{gs}	Gate-Source Charge		-	8	-	
Q _{gd}	Gate-Drain Charge		-	10	-	

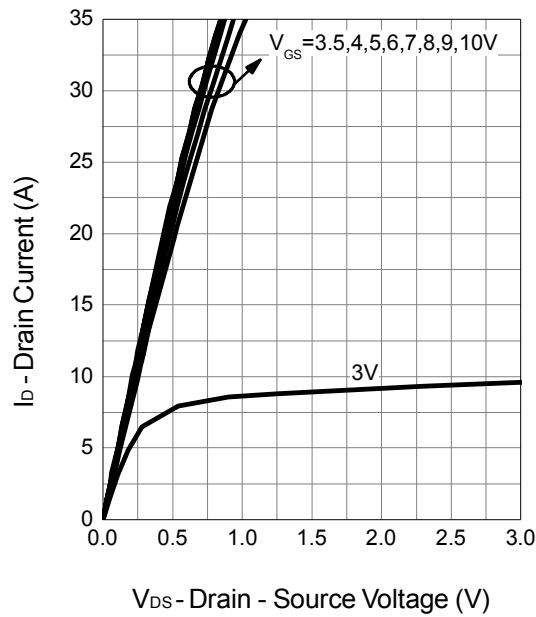
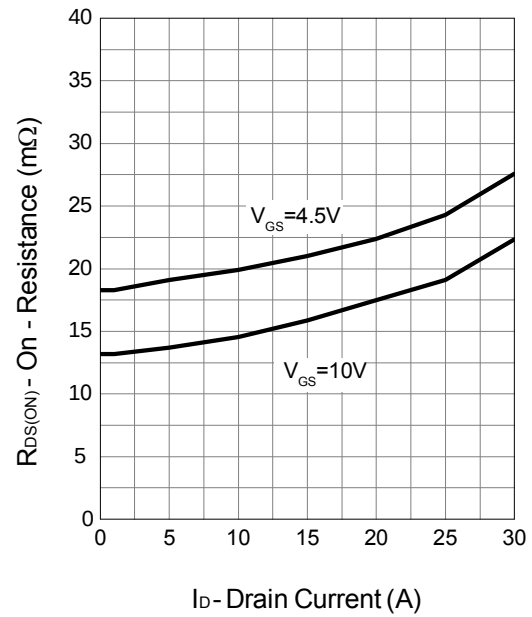
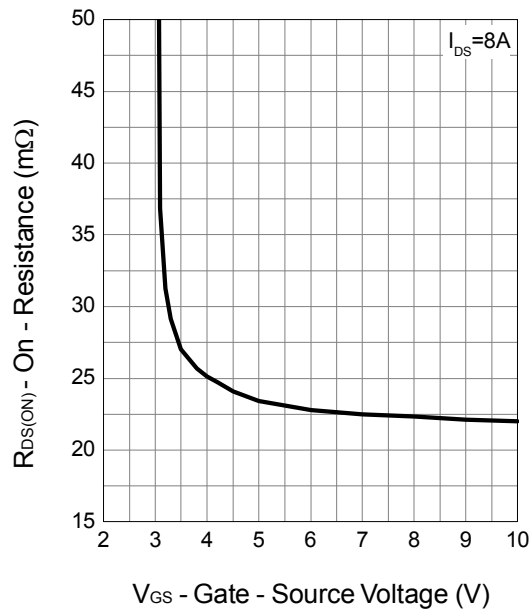
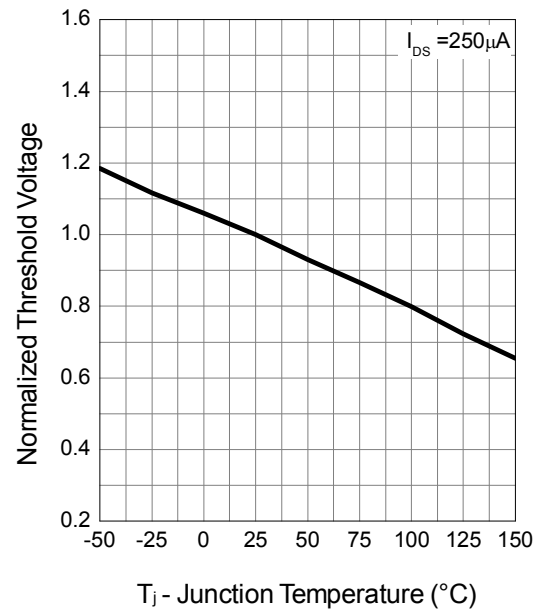
Note c: Pulse test; pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%$.

d: Guaranteed by design, not subject to production testing.

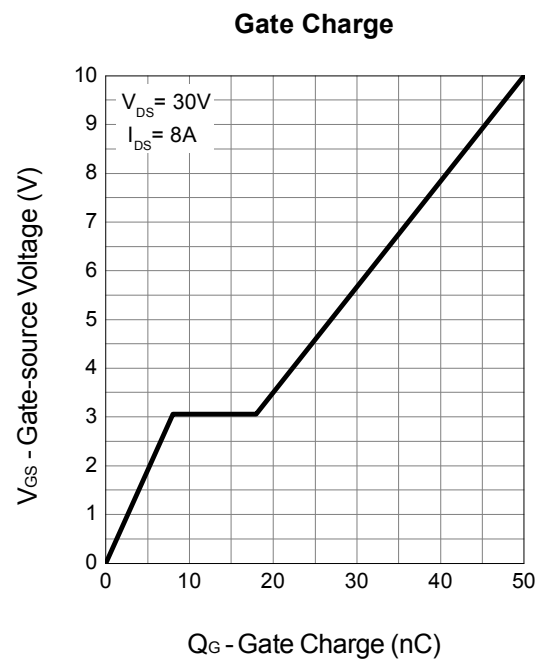
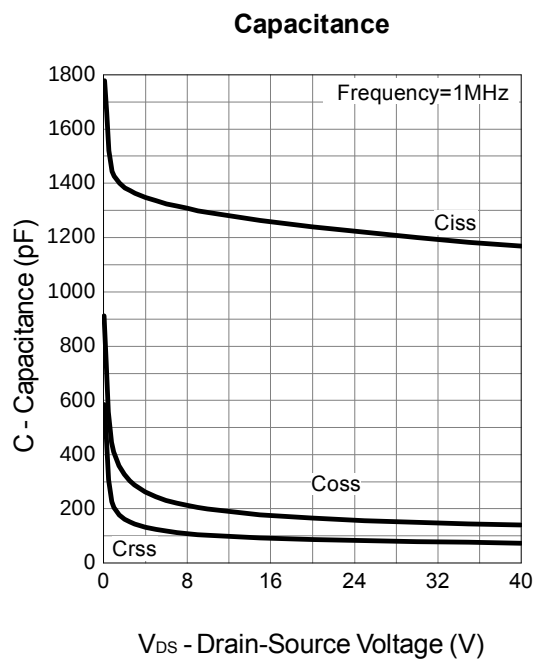
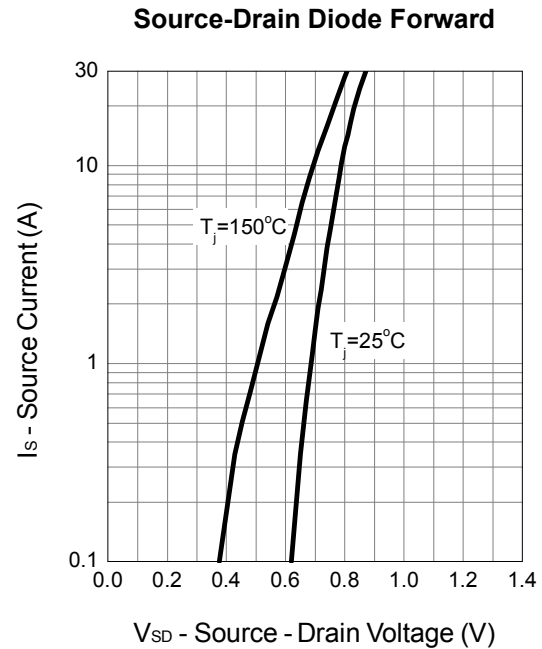
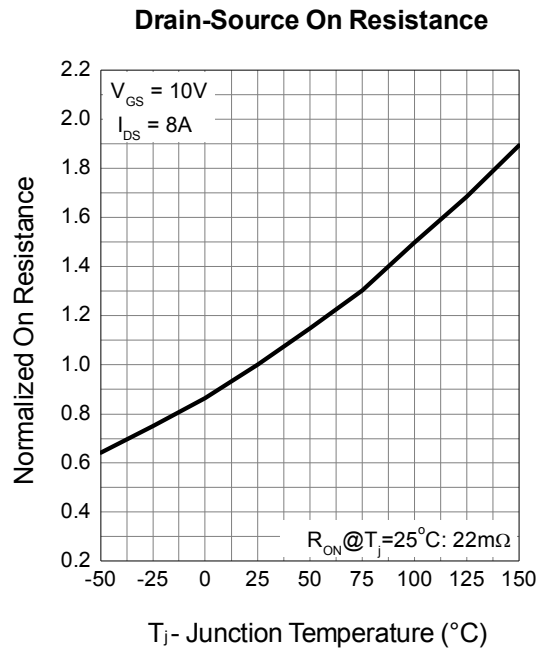
Typical Operating Characteristics



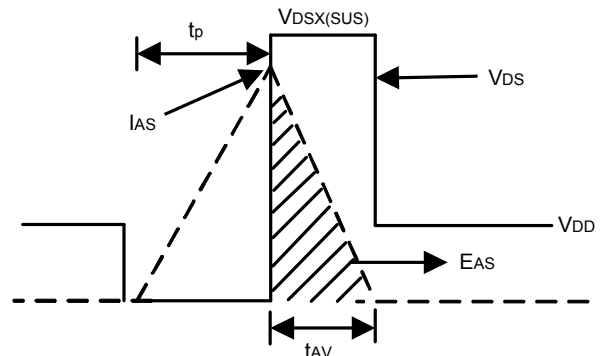
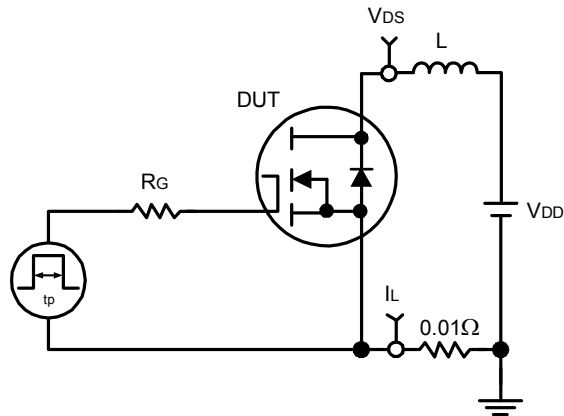
Typical Operating Characteristics (Cont.)

Output Characteristics

Drain-Source On Resistance

Gate-Source On Resistance

Gate Threshold Voltage


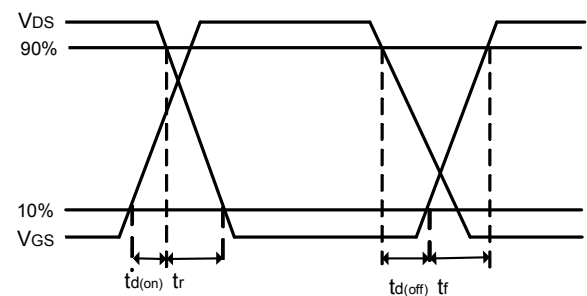
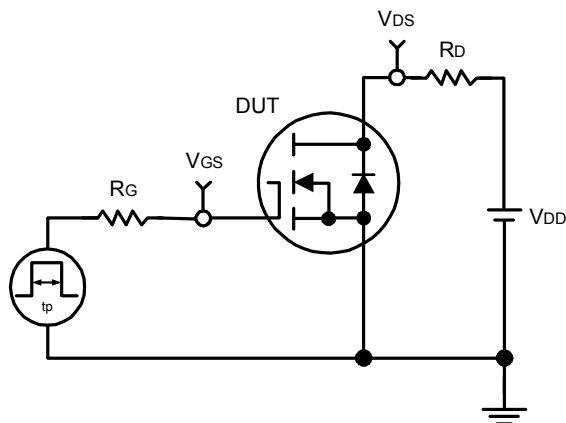
Typical Operating Characteristics (Cont.)



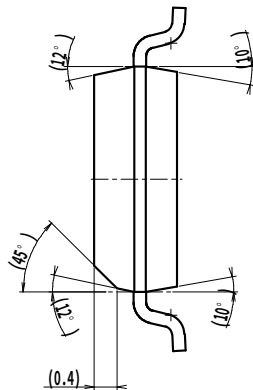
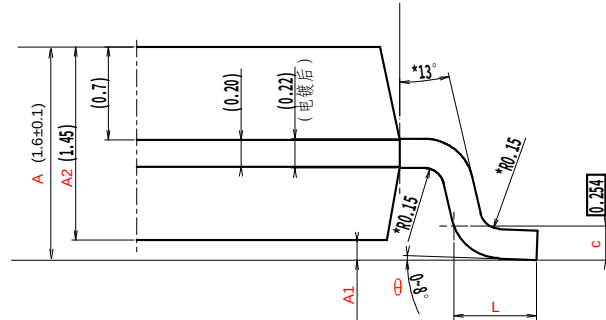
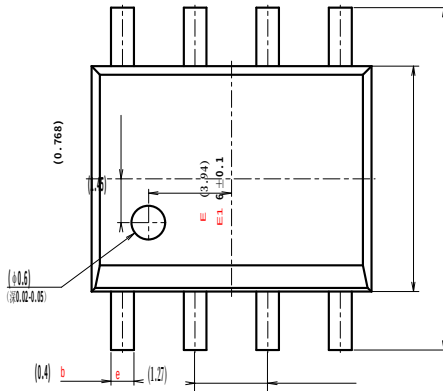
Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



SOP8 PACKAGE OUTLINE



字符	Dimension millimeters		
	Min	Standard	Max
A	1.500	1.600	1.700
A1	0.040	0.080	0.150
A2	1.350	1.450	1.550
b	0.300	0.400	0.500
c	0.220	0.254	0.280
D	4.800	4.900	5.000
E	3.840	3.940	4.040
E1	5.900	6.000	6.100
e		1.27 (BSC)	
L	0.400	0.550	0.700
θ	0°		8°

